

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
20V	13mΩ@4.5V	7A
	18mΩ@2.5V	

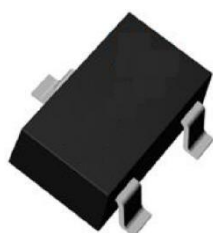
Feature

- High power and current handling capability
- Surface mount package

Application

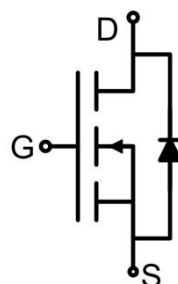
- Battery Switch
- DC/DC Converter

Package

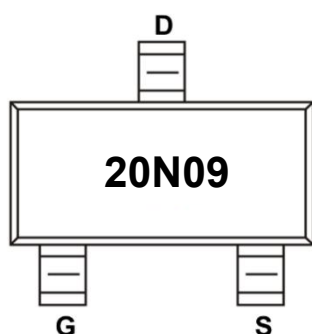


SOT-23-3L

Circuit diagram



Marking



Absolute maximum ratings ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	7	A
Pulsed Drain Current	I_{DM}	28	A
Power Dissipation	P_D	1.25	W
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	100	$^{\circ}\text{C}/\text{W}$
Operating Junction Temperature	T_J	$-55 \sim +150$	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	$-55 \sim +150$	$^{\circ}\text{C}$

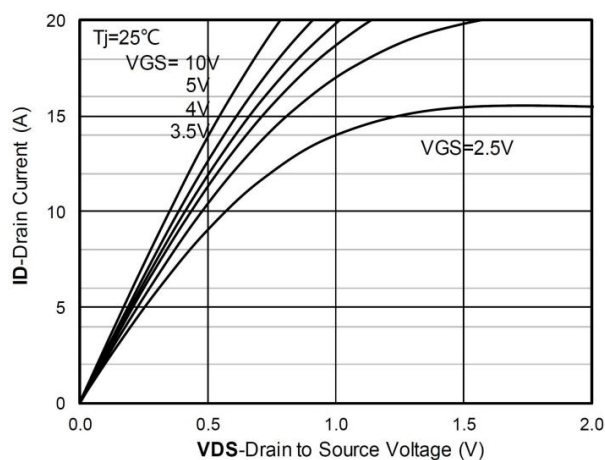
Electrical characteristics ($T_A=25^{\circ}\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250μA	20			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =16V, V _{GS} =0V			1	μA
Gate-body leakage current	I _{GSS}	V _{DS} =0V, V _{GS} =±12V			±100	nA
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.5	0.7	1.5	V
Drain-source on-resistance	R _{DS(on)}	V _{GS} =4.5V, I _D =6A		10	13	mΩ
		V _{GS} =2.5V, I _D =5A		13	18	
Dynamic characteristics ¹⁾						
Input Capacitance	C _{iss}	V _{DS} =10V, V _{GS} =0V, f =1MHz		900		pF
Output Capacitance	C _{oss}			162		
Reverse Transfer Capacitance	C _{rss}			105		
Total Gate Charge	Q _g	V _{DS} =10V, V _{GS} =10V, I _D =20A		15		nC
Gate-Source Charge	Q _{gs}			1.8		
Gate-Drain Charge	Q _{gd}			2.8		
Turn-on delay time	t _{d(on)}	V _{DS} =10V, V _{GS} =10V, I _D =5A R _G =3Ω		4.5		nS
Turn-on rise time	t _r			9.2		
Turn-off delay time	t _{d(off)}			18.7		
Turn-off fall time	t _f			3.3		
Source-Drain Diode characteristics						
Diode Forward Current	I _S				7	A
Diode Forward voltage	V _{SD}	V _{GS} =0V, I _S =1A, T _J =25℃			1.2	V

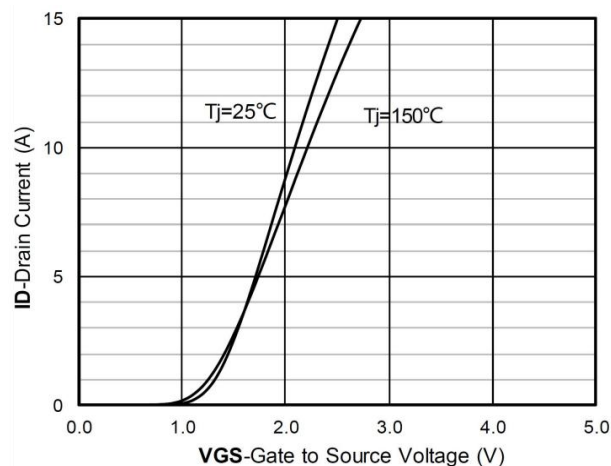
Notes:

1) Guaranteed by design, not subject to production testing.

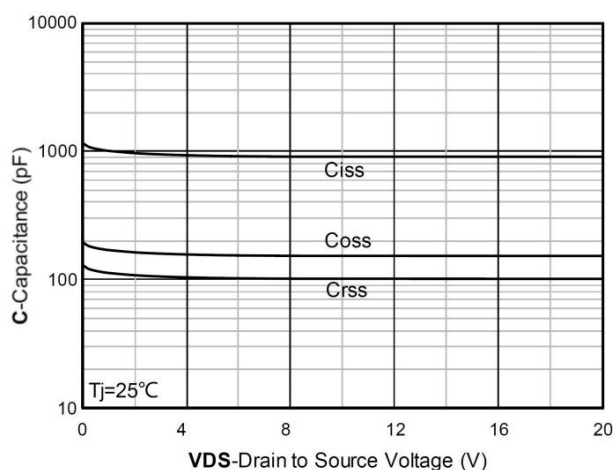
Typical Characteristics



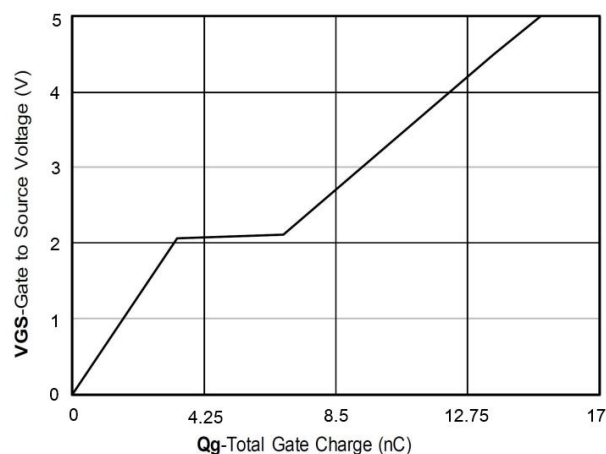
Output Characteristics



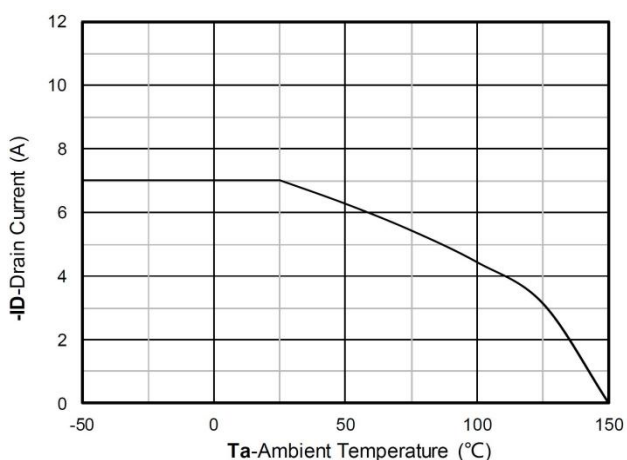
Transfer Characteristics



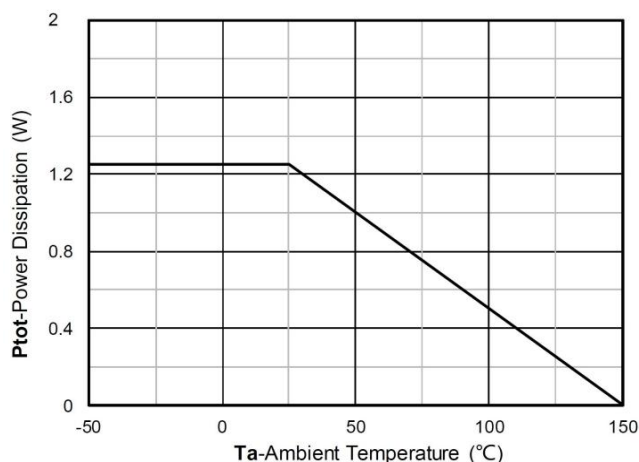
Capacitance Characteristics



Gate Charge

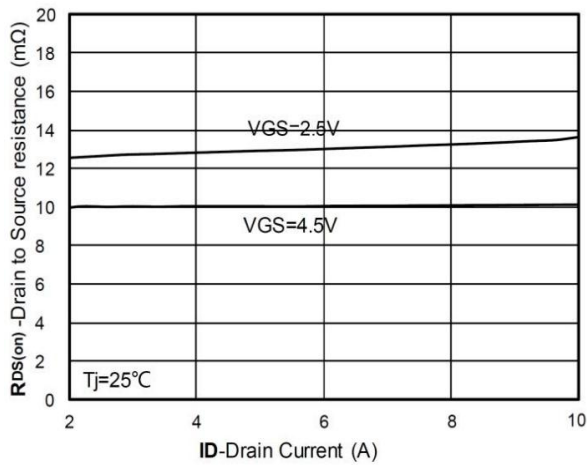


Current dissipation

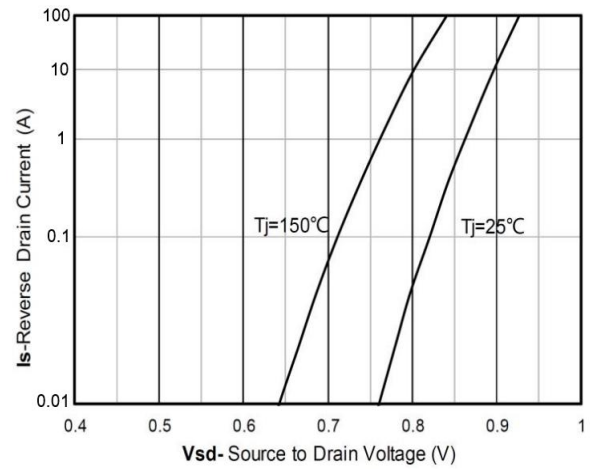


Power dissipation

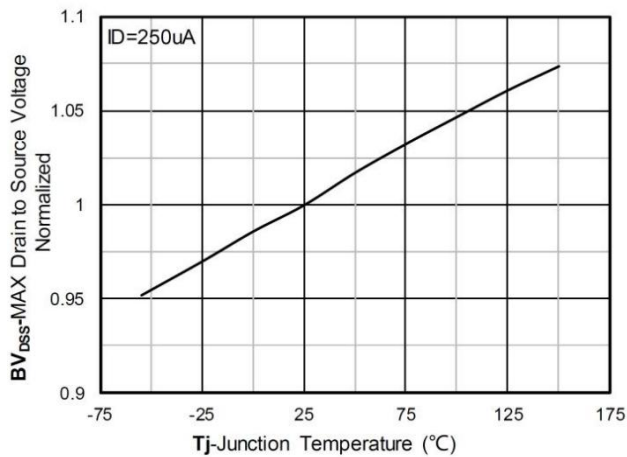
Typical Characteristics



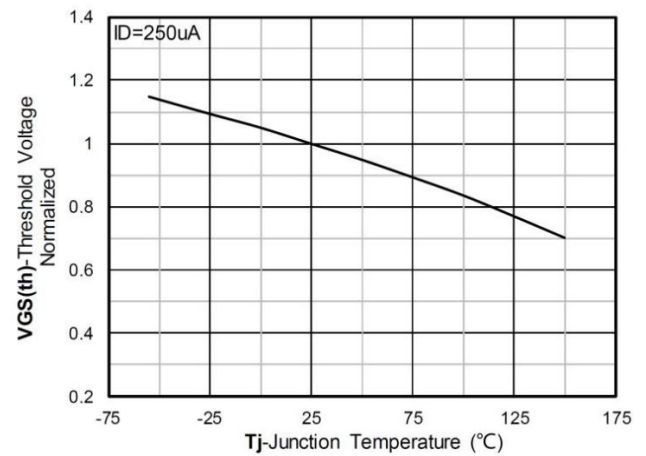
$R_{DS(on)}$ VS Drain Current



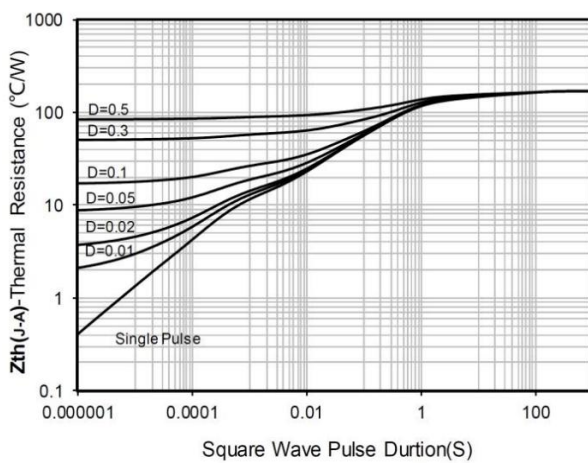
Forward characteristics of reverse diode



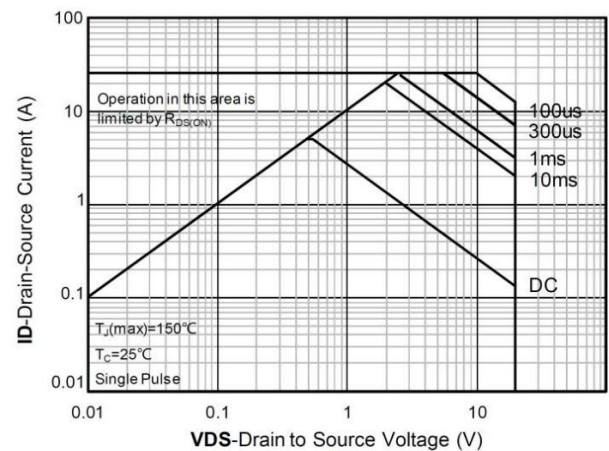
Normalized breakdown voltage



Normalized Threshold voltage

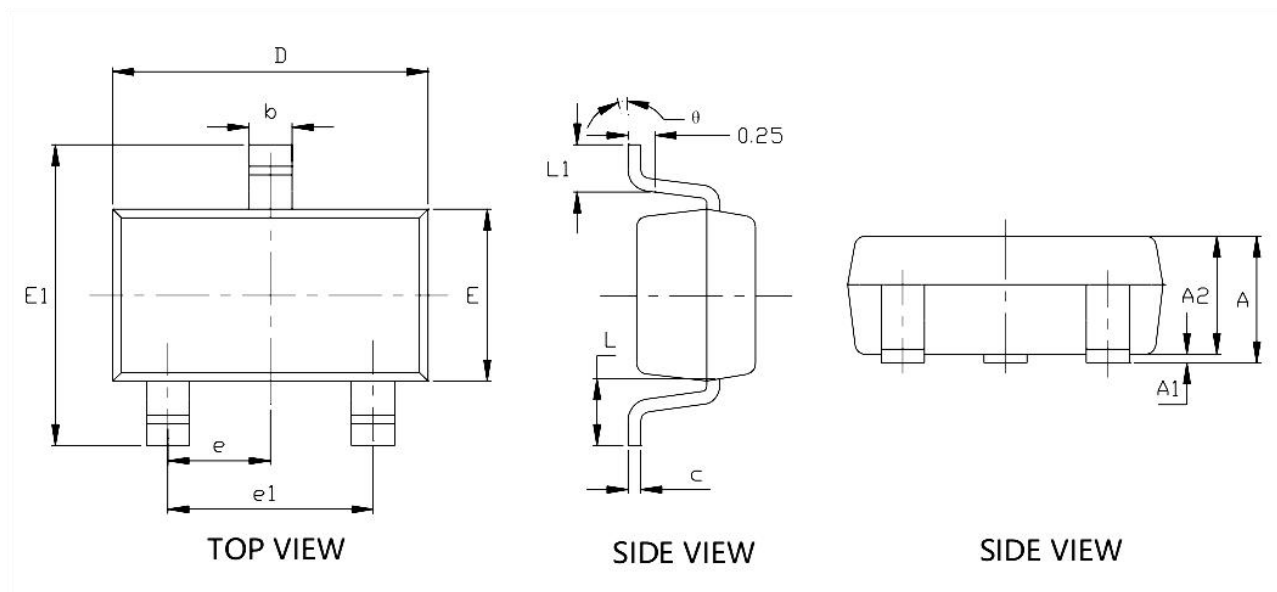


Maximum Transient Thermal Impedance



Safe Operation Area

SOT-23-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.600 REF.		0.024 REF.	
L1	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°